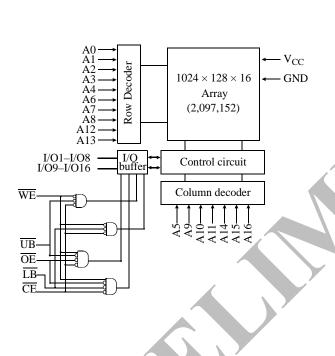
### **3.3 V 128K × 16 CMOS SRAM**

#### **Features**

- Industrial and commercial temperature
- Organization: 131,072 words  $\times$  16 bits
- Center power and ground pins
- High speed
  - 10/12/15/20 ns address access time
  - 4/5/6/7 ns output enable access time
- Low power consumption: ACTIVE
  - 650 mW/max @ 10 ns
- Low power consumption: STANDBY

- 28.8 mW /max CMOS
- Individual byte read/write controls
- Easy memory expansion with  $\overline{CE}$ ,  $\overline{OE}$  inputs
- TTL- and CMOS-compatible, three-state I/O
- 44-pin JEDEC standard packages
  - TSOP 2
- ESD protection ≥ 2000 volts
- Latch-up current ≥ 200 mA

### Logic block diagram



### Pin arrangement for TSOP 2

A0		10	44	A16
<b>A</b> 1		2	43	A15
A2		3	42	A14
A3\		4	41	<del>OE</del>
A4		5	40	UB
CE		6	39	LB
I/O1	Y	7	38	I/O16
I/O2		8	37	I/O15
I/O3	=	9	36	I/O14
I/O4		10	35	I/O13
$V_{CC}$		11	34	GND
GND		12	33	
I/O5		13		V <sub>CC</sub>
I/O6		14	32	I/O12
I/O7		15	30	I/O11 I/O10
I/O8		16	29	I/O9
WE		17	28	NC
A5		18	27	A13
A6		19	26	A12
A7		20	25	A11
A8		21	24	A10
A9		22	23	NC

### **Selection guide**

		-10	-12	-15	-20	Unit
Maximum address access time		10	12	15	20	ns
Maximum output enable access time		4	5	6	7	ns
Maximum operating current	Industrial	180	160	140	110	mA
iviaximum operating current	Commercial	170	150	130	100	mA
Maximum CMOS standby current	•	8	8	8	8	mA



### **Functional description**

The AS7C32098A is a high-performance CMOS 2,097,152-bit Static Random Access Memory (SRAM) device organized as 131,072 words  $\times$  16 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times ( $t_{AA}$ ,  $t_{RC}$ ,  $t_{WC}$ ) of 10/12/15/20 ns with output enable access times ( $t_{OE}$ ) of 4/5/6/7 ns are ideal for high-performance applications. The chip enable input  $\overline{CE}$  permits easy memory expansion with multiple-bank memory systems.

When  $\overline{\text{CE}}$  is high the device enters standby mode. The device is guaranteed not to exceed 28.8mW power consumption in CMOS standby mode. A write cycle is accomplished by asserting write enable ( $\overline{\text{WE}}$ ) and chip enable ( $\overline{\text{CE}}$ ). Data on the input pins I/O1–I/O16 is written on the rising edge of  $\overline{\text{WE}}$  (write cycle 1) or  $\overline{\text{CE}}$  (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable ( $\overline{\text{OE}}$ ) or write enable ( $\overline{\text{WE}}$ ).

A read cycle is accomplished by asserting output enable  $(\overline{OE})$  and chip enable  $(\overline{CE})$ , with write enable  $(\overline{WE})$  high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive, or write enable is active, output drivers stay in high-impedance mode.

The device provides multiple center power and ground pins, and separate byte enable controls, allowing individual bytes to be written and read.  $\overline{LB}$  controls the lower bits, I/O1–I/O8, and  $\overline{UB}$  controls the higher bits, I/O9–I/O16.

All chip inputs and outputs are TTL- and CMOS-compatible, and operation is for 3.3V (AS7C32098A) supply. The device is available in the JEDEC standard TSOP 2 package.

#### **Absolute maximum ratings**

Parameter	Symbol	Min	Max	Unit
Voltage on V <sub>CC</sub> relative to GND	$V_{t1}$	-0.50	+5.0	V
Voltage on any pin relative to GND	$V_{t2}$	-0.50	V <sub>CC</sub> +0.50	V
Power dissipation	$P_{D}$	-	1.5	W
Storage temperature (plastic)	T <sub>stg</sub>	-65	+150	°C
Ambient temperature with V <sub>CC</sub> applied	T <sub>bias</sub>	-55	+125	°C
DC current into outputs (low)	I <sub>OUT</sub>	_	±20	mA

Note: Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### Truth table

CE	WE	<del>OE</del>	LB	<del>UB</del>	I/O1–I/O8	I/O9-I/O16	Mode
Н	X	X	X	X	High Z	High Z	Standby (I <sub>SB</sub> , I <sub>SB1</sub> )
L /	Н	Н	X	X	High 7	High 7	Outant disable (I )
L	X	X	Н	Н	High Z	High Z	Output disable (I <sub>CC</sub> )
			L	Н	D <sub>OUT</sub>	High Z	
L	Н	L	Н	L	High Z	D <sub>OUT</sub>	Read (I <sub>CC</sub> )
			L	L	D <sub>OUT</sub>	D <sub>OUT</sub>	
			L	Н	$D_{IN}$	High Z	
L	L	X	Н	L	High Z	$D_{IN}$	
			L	L	$D_{IN}$	$D_{IN}$	Write (I <sub>CC</sub> )

Key: X = Don't care, L = Low, H = High.



## **Recommended operating conditions**

Parameter	Symbol	Min	<b>Typical</b>	Max	Unit	
Supply voltage		V <sub>CC</sub> (10/12/15/20)	3.0	3.3	3.6	V
Input voltage		${ m V_{IH}}^{**}$	2.0	_	$V_{CC} + 0.5$	V
imput voitage		${ m V_{IL}}^*$	-0.5	_	0.8	V
Ambient operating temperature	commercial	$T_{A}$	0	_	70	°C
Amoreni operating temperature	industrial	$T_{A}$	-40	_	85	°C

## DC operating characteristics (over the operating range) $^{I}$

				_]	10	_	12	-	15	-2	20	
Parameter	Symbol	<b>Test conditions</b>		Min	Max	Min	Max	Min	Max	Min	Max	Unit
Input leakage current	$ I_{LI} $	$V_{CC} = Max$ $V_{IN} = GND$ to $V_{C}$	cc		1	-	1	1	1	1	1	μA
Output leakage current	$ I_{LO} $	$V_{CC} = \underline{Max}$ $\overline{CE} = V_{\underline{IH}} \text{ or } \overline{OE} = V_{\underline{IL}}$ or $\overline{WE} = V_{\underline{IL}}$ $V_{\underline{I/O}} = \overline{GND} \text{ to } V_{\underline{O}}$		-	1	1	1	1	1	1	1	μА
Operating power supply current	I <sub>CC</sub>	$V_{CC} = Max$ $\overline{CE} \le V_{IL}, f = f_{max} I_{OUT} = 0mA$	Industrial  Commercial	-	180 170	-	160 150	-	140 130	-	110 100	mA mA
G. H	$I_{SB}$	$\frac{V_{CC} = Max}{CE \ge V_{IH}, f = Ma}$	ıx	-	60	1	60	1	60	1	60	mA
Standby power supply current	$I_{SB1}$	$ \frac{V_{CC} = Max}{\overline{CE}} \ge V_{CC} - 0.2V, V_{IN} \ge V_{CC} $ $ V_{IN} \le 0.2V, f = 0 $		_	8	-	8	-	8	-	8	mA
Output voltage	V <sub>OL</sub>	$I_{OL} = 8 \text{ mA}, V_{CC} =$		ı	0.4	_	0.4	_	0.4	-	0.4	V
- mgc	V <sub>OH</sub>	$I_{OH} = -4 \text{ mA}, V_{CC} =$	Min	2.4	_	2.4	_	2.4	-	2.4	-	V

# Capacitance (f = 1MHz, $T_a = 25^{\circ} C$ , $V_{CC} = NOMINAL$ )<sup>4</sup>

Parameter	Symbol	Signals	Test conditions	Max	Unit
Input capacitance	$C_{IN}$	$A, \overline{CE}, \overline{WE}, \overline{OE}, \overline{UB}, \overline{LB}$	$V_{IN} = 0V$	6	pF
I/O capacitance	C <sub>I/O</sub>	I/O	$V_{IN} = V_{OUT} = 0V$	8	pF

 $<sup>{*\</sup>atop **}V_{IL}$  min = -1.0V for pulse width less than 5ns.  $V_{IH}$  max =  $V_{CC}$  + 2.0V for pulse width less than 5ns.



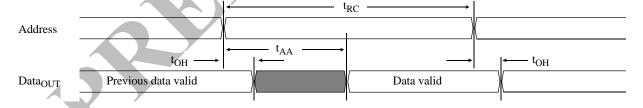
# Read cycle (over the operating range) $^{2,8}$

		-1	10	-3	12	-1	15	-2	20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Notes
Read cycle time	t <sub>RC</sub>	10	-	12	_	15	_	20	1	ns	
Address access time	$t_{AA}$	-	10	_	12	_	15	_	20	ns	
Chip enable (\overline{CE}) access time	t <sub>ACE</sub>	_	10	_	12	_	15	_	20	ns	
Output enable (OE) access time	t <sub>OE</sub>	_	4	_	5	_	6		7	ns	
Output hold from address change	t <sub>OH</sub>	3	_	3	_	3	_	3	1	ns	4
CE Low to output in low Z	t <sub>CLZ</sub>	3	_	3	_	3	-	3	- >	ns	3,4
TE High to output in high Z	t <sub>CHZ</sub>	_	5	_	6	_	7	_	9	ns	3,4
OE Low to output in low Z	t <sub>OLZ</sub>	0	_	0	_	0	-	0	_	ns	3,4
OE High to output in high Z	t <sub>OHZ</sub>	_	5	_	6	-	7	_	9	ns	3,4
LB, UB access time	$t_{BA}$	-	5	-	6	-	7	_	8	ns	
LB, UB Low to output in low Z	$t_{ m BLZ}$	0	_	0	-	0	_	0	1	ns	
LB, UB High to output in high Z	t <sub>BHZ</sub>	_	5	-	6	r –	7	_	9	ns	
Power up time	t <sub>PU</sub>	0	H	0	-	0	_	0	_	ns	4
Power down time	t <sub>PD</sub>		10	-	12	-	15	-	20	ns	4

## Key to switching waveforms

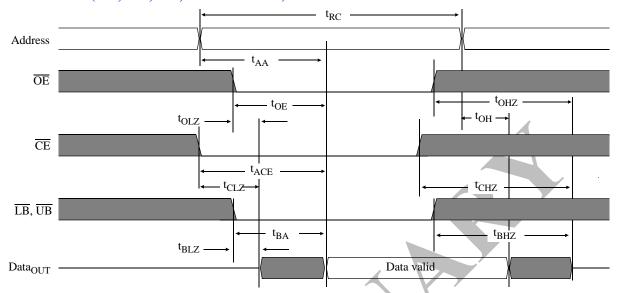
Rising input Undefined/don't care

# Read waveform 1 (address controlled)<sup>5,6,8</sup>





# Read waveform 2 (CE, OE, UB, LB controlled)<sup>5,7,8</sup>

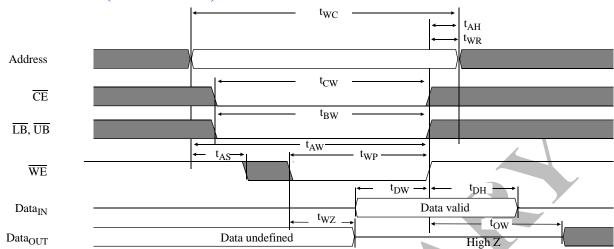


## Write cycle (over the operating range)<sup>9</sup>

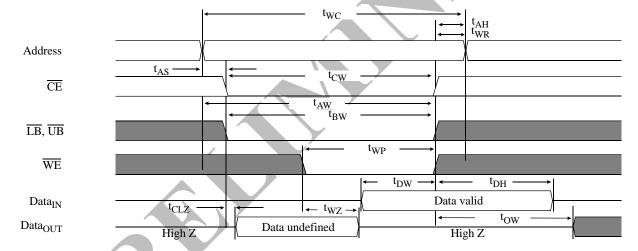
		_	10	_	12	-	15		20		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Unit	Note
Write cycle time	$t_{WC}$	10		12	_	15	_	20	-	ns	
Chip enable $\overline{\text{(CE)}}$ to write end	t <sub>CW</sub>	1	1	8	-	10	_	12	-	ns	
Address setup to write end	t <sub>AW</sub>	7	-	8	-	10	-	12	-	ns	
Address setup time	t <sub>AS</sub>	0	<b>)</b> -	0	_	0	_	0	_	ns	
Write pulse width $(\overline{OE} = High)$	t <sub>WP1</sub>	7	_	8	-	10	-	12	-	ns	
Write pulse width $(\overline{OE} = Low)$	t <sub>WP2</sub>	10	_	12	_	15	_	20	_	ns	
Write recovery time	t <sub>WR</sub>	0	-	0	_	0	_	0	_	ns	
Address hold from end of write	t <sub>AH</sub>	0	_	0	-	0	-	0	-	ns	
Data valid to write end	$t_{DW}$	5	_	6		7	_	9	_	ns	
Data hold time	t <sub>DH</sub>	0	-	0	_	0	_	0	_	ns	3,4
Write enable to output in High-Z	t <sub>WZ</sub>	0	5	0	6	0	7	0	9	ns	3,4
Output active from write end	t <sub>OW</sub>	3	-	3	_	3	-	3	_	ns	3,4
Byte enable Low to write end	$t_{\mathrm{BW}}$	7	_	8	_	10	_	12	_	ns	3,4



# Write waveform 1(WE controlled)9

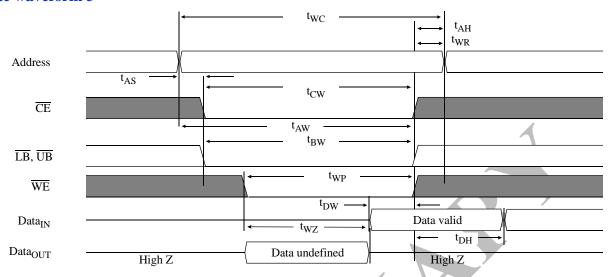


## Write waveform $2 (\overline{CE} \text{ controlled})^9$





### Write waveform 3 9



#### **AC** test conditions

- Output load: see Figure B.
- Input pulse level: GND to 3.0V. See Figure A.
- Input rise and fall times: 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

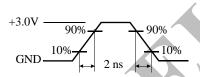
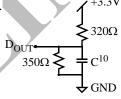


Figure A: Input pulse



D.

The venin equivalent:  $D_{OU} = 168\Omega + 1.728V$ 

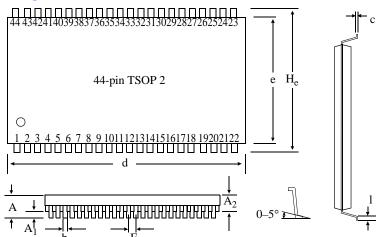
Figure B: 3.3V Output load

#### Notes

- 1 During  $V_{CC}$  power-up, a pull-up resistor to  $V_{CC}$  on  $\overline{CE}$  is required to meet  $I_{SB}$  specification.
- 2 For test conditions, see AC Test Conditions, Figures A and B.
- 3  $t_{CLZ}$  and  $t_{CHZ}$  are specified with  $C_L = 5 pF$  as in Figure B. Transition is measured  $\pm 500 mV$  from steady-state voltage.
- 4 This parameter is guaranteed, but not tested.
- $\overline{\text{WE}}$  is High for read cycle.
- 6  $\overline{\text{CE}}$  and  $\overline{\text{OE}}$  are Low for read cycle.
- 7 Address valid prior to or coincident with  $\overline{\text{CE}}$  transition Low.
- 8 All read cycle timings are referenced from the last valid address to the first transitioning address.
- 9 All write cycle timings are referenced from the last valid address to the first transitioning address.
- 10 C=30pF, except on High Z and Low Z parameters, where C=5pF.



## **Package dimensions**



	<b>44-pin</b> ′	TSOP 2				
	Min (mm)	Max (mm)				
A		1.2				
$\mathbf{A_1}$	0.05	0.15				
A <sub>2</sub>	0.95	1.05				
b	0.3	0.45				
c	0.12	0.21				
d	18.31	18.52				
e	10.06	10.26				
H <sub>e</sub>	11.68	11.94				
E	0.80 (t	ypical)				
1	0.40	0.60				



## **Ordering Codes**

Package	Temperature	10 ns	12 ns	15 ns	20 ns
TSOP 2	Commercial	AS7C32098A-10TC	AS7C32098A-12TC	AS7C32098A-15TC	AS7C32098A-20TC
1501 2	Industrial	AS7C32098A-10TI	AS7C32098A-12TI	AS7C32098A-15TI	AS7C32098A-20TI

Note: Add suffix 'N' to the above part numbers for Lead Free Parts. (Ex: AS7C32098A - 10TCN)

## Part numbering system

	•					
AS7C	X	2098A	-XX	T	X	X
SRAM prefix	Voltage: 3 - 3.3V CMOS	Device number		Package: T: TSOP 2	Temperature ranges: C: Commercial, 0°C to 70°C I: Industrial, -40°C to 85°C	N = Lead Free Parts







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